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Destructive Little-Parks Effect in a Full-Shell Nanowire-Based Transmon

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A semiconductor transmon with an epitaxial Al shell fully surrounding an InAs nanowire core is investigated in the low $E_J/E_C$ regime. Little-Parks oscillations as a function of flux along the hybrid wire axis are destructive, creating lobes of reentrant superconductivity separated by a metallic state at a half quantum of applied flux. In the first lobe, phase winding around the shell can induce topological superconductivity in the core. Coherent qubit operation is observed in both the zeroth and first lobes. Splitting of parity bands by coherent single-electron coupling across the junction is not resolved beyond line broadening, placing a bound on Majorana coupling, $E_M/h < 10$ MHz, much smaller than the Josephson coupling $E_J/h \sim 4.7$ GHz.

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Variants of the conventional metallic transmon qubit [1,2] based on a semiconductor nanowires (NWs) with an epitaxial superconducting shell have appeared recently and shown great promise for qubit applications, offering atomically precise interfaces and electrostatic control of junction properties [3–7]. By now, qubit spectroscopy [3], coherence [4], two-qubit operation [5], gate-controlled qubit coupling [8], and dc monitoring [9] have been demonstrated, along with investigations of applied magnetic field [7], junction Andreev bound states [6,10], anharmonicity [11], charge dispersion [12,13], spin [14], and parity protection [15]. However, axial flux effects from a fully surrounding Al shell on Josephson coupling have not been considered previously. This is more than a detail. In these small-diameter systems, it is known that an axial magnetic field applied to a cylindrical superconducting shell can give rise to an extreme form of the Little-Parks effect [16] characterized by flux-driven reentrant superconductivity [17–19], and, in semiconductor-superconductor hybrids to a possibility to realize topological superconductivity [20].

Proposals to realize transmons based on topological superconductors typically require sizeable applied magnetic fields to drive the system into the topological phase [21–25]. In these schemes, a properly oriented magnetic field splits the spin-orbit band, typically requiring $\sim 1$ T to reach the topological regime [26], a challenge to most superconducting technologies [7] with some exceptions [27]. Recent experiments and theory indicate that topological superconductivity can be induced in a NW with a fully surrounding superconducting shell by winding the superconducting phase around the wire using magnetic flux rather than Zeeman coupling, requiring lower fields ($\sim 0.1$ T) to reach the first reentrant superconducting lobe in the destructive Little-Parks effect regime [20].

In an ideal topological transmon, a pair of Majorana zero modes (MZMs) straddle the Josephson junction, and are coupled via coherent single-electron tunneling with a characteristic energy scale $E_M$, which accompanies the usual Josephson coupling, $E_J$, across the junction [23,28,29]. From the perspective of circuit quantum electrodynamics spectroscopy, $E_M$ splits the parity-preserving level crossings thereby doubling the number of spectral lines [23]. The prediction of $E_M$ from device parameters is difficult as $E_M$ depends sensitively on the potential in the junction. While $E_M$ is expected to increase as the junction barrier is lowered, its value is likely limited by the presence of additional transport channels within the subgap spectrum of the junction [25,30].

In this Letter, we investigate InAs/Al hybrid semiconductor-based NWs with a fully surrounding superconducting shell, comparing qubit spectra and coherence in the zeroth (trivial) lobe to the first reentrant lobe, corresponding to roughly one flux quantum ($\Phi_0 = h/2e$) of applied magnetic field through the Al shell, where topological superconductivity is anticipated. We focus on the offset-charge-sensitive transmon regime [31–34] to facilitate a direct examination of the parity of the superconducting island. Coherence was observed via spectral and time-domain measurements in both the zeroth and first superconducting lobes. The destructive Little-Parks effect causes a field-dependent superconducting gap, and the destruction of superconductivity altogether between lobes, around an applied flux of $\Phi_0/2$. We model the effects of
flux on qubit frequency, finding good agreement with
experiment. We do not observe clear splittings of gate-
modulated charge dispersion bands. Such splitting would
reflect coherent Majorana coupling anticrossing the parity
bands. This allows us to set a bound on Majorana coupling
across the semiconductor junction, $E_M/h < 10 \text{ MHz}$.

A chip containing six NW hybrid transmons and individual readout resonators is shown in Fig. 1(a). The
circuit ground plane, qubit island, and all control and
readout elements (electrostatic gates, on-chip gate filters,
readout resonator, transmission line, and NbTiN crossovers
on all control lines) were fabricated from sputtered NbTiN,
patterned using e-beam lithography and reactive ion etching
on a high-resistivity silicon wafer. The charging energy
of the qubit island capacitor with a charging energy $E_C$.
(b) Scanning electron micrographs of two investigated devices: top—
device 1, bottom—device 2. Gate voltage $V_C$ in both devices
controlled both qubit frequency (large range) and offset charge
(small range). Device 1 was decoupled from dc lead (right side)
with negative $V_{\text{FETC}}$. The capacitor island is connected in the
middle of device 1 and on right side in device 2. (c) False colored
enlargement of the semiconductor junction (red) in device 2 where
Al shell (yellow) is removed, controlled by gate below the
dielectric (green). (d) Schematic cross section of the hybrid
nanowire and substrate stack, showing mean diameter, $2R$, shell
thickness, $t$ and direction of applied field $B$.

The inset in Fig. 1(a) shows an enlargement of a sample
area and a transmon island capacitor. The NW is approx-
imately 10 μm long and resides on top of a HfO$_2$ dielectric
that separates it from the bottom gates. Eight working
devices were measured and showed similar results. We
present data from two representative devices (device 1 and
device 2) shown in Fig. 1(b). For device 1, one side of the
NW is connected to ground plane and the other makes an
ohmic contact with NbTiN, allowing dc monitoring that
can be connected and disconnected in situ [9] using
gate voltage $V_{\text{FETC}}$. The contact in the middle of the
NW connects the junction to the qubit island. Device 2 is
a simpler design, with one side of the NW connected to
the qubit island and the other to the ground plane.
All measurements are performed in a BlueFors XLD
dilution refrigerator with a base temperature of 20 mK
and $1 - 6$ vector magnet.

Figure 1(c) shows an enlargement (device 2) of the gate-
controlled Josephson junction in the full-shell NW. The
junction was formed by wet etching the Al shell in a
100–150 nm region defined by electron-beam litho-
graphy. The voltage $V_C$ on the bottom gate was used to
tune the junction coupling. The same gate was used to tune
both the qubit frequency, on a large voltage range, and the
offset charge, on a small voltage range. The schematics of
the cross section of the full-shell InAs/Al NW together with
a substrate material stack is shown in Fig. 1(d).

Measurements were performed using two-tone spectro-
scopy, where a microwave drive pulse is followed by a
readout tone close to the cavity frequency. After the readout
tone enters the readout cavity, it interacts with the
respective resonator before being amplified by a traveling
wave parametric amplifier at base temperature, high elec-
tron mobility transistor amplifier at 4 K, and additional
amplification at room temperature. The signal is then
mixed to an intermediate frequency and sampled followed
by digital heterodyne detection to extract the cavity
response, $V_H$.

As a first signature of the Little-Parks lobe structure,
we examine qubit frequency as a function of axial magnetic
field, $B$. The zero-field qubit frequency was set to
$-4.3 \text{ GHz (} V_C \sim -2.5 \text{ V)}$ slightly below the readout res-
onator frequency, $f_r \sim 5.29 \text{ GHz}$ for device 1. A map of the
amplitude of the heterodyne demodulated transmission $V_H$
(line average subtracted) as a function of qubit drive
frequency $f_d$ and magnetic field $B$ is shown in Fig. 2(a).
At each field step the readout frequency was adjusted by
tracking the frequency of the resonator. At low fields,
$B \leq 40 \text{ mT}$, the NW is in the zeroth lobe, with a trivial
proximity effect from the shell, and a field dependent gap,
$\Delta(B)$ with its maximum value, $\Delta_0$ at $B = 0$. At inter-
mediate fields, around $50 \text{ mT}$, the qubit frequency falls
rapidly, the resonance broadens and disappears.
This behavior is associated with the destructive regime
around applied flux $\Phi_0/2$, where $\Delta(B)$ goes to zero
and superconductivity is destroyed [19,20]. At higher fields,
$B \sim 60–120 \text{ mT}$ the qubit is recovered and shows similar
behavior to the low-field regime with a maximum qubit
frequency around $90 \text{ mT}$, slightly reduced from its
zero-field value. This recovery of qubit frequency reflects
the underlying lobe structure of superconductivity in the
NW [19]. In the first lobe, one vortex has entered the shell,
the superconducting phase twists once around the wire

FIG. 1. (a) Optical micrograph of the sample chip showing
multiple separate qubit readout resonators connected to a single
readout line. The inset shows an enlargement of a sample area and
a transmon island capacitor with a charging energy $E_C$. (b) Scan-
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the superconducting phase twists once around the wire
The winding number (c) favourably is determined by minimizing a given magnetic field dependence of the pairing energy.

The frequency $f_Q$ of the superconducting lobe, qubit frequency $f_Q$ decreases with increasing $B$; (ii) destructive regime, around half flux quantum $\Phi_0/2 \sim 50 \text{ mT}$, qubit coherence is lost; (iii) higher fields ($60\text{–}120 \text{ mT}$), first lobe, coherence is recovered with slightly reduced $f_Q$; and (iv) second destructive regime at $\sim 135 \text{ mT}$ where coherence is again lost. (b) Experiment (black points) and theory (orange curve) for qubit frequency, $f_Q$. Width of theory curve marks 3rd and 97th percentiles of the fit.

We relate the field dependent gap $\Delta(B)$ to qubit frequency $f_Q$ assuming the proportionality $E_J(B) \propto \Delta(B)$ and taking $E_J \gg E_C$, which yields a scaling relation $f_Q = f_0 d(B)^{1/2}$ where $d(B) = \Delta(B)/\Delta_0$. A numerical fit was then used to determine the four fit parameters: $R = 81 \text{ nm}$, $t = 36 \text{ nm}$, $\xi = 139 \text{ nm}$, and $f_0 = 4.34 \text{ GHz}$, yielding the theory curve in Fig. 2(b), which is in good agreement with experiment. The extracted geometrical fit parameters $t$ and $R$ are comparable to the values estimated from the electron micrograph in Fig. 1(b).

FIG. 2. (a) Two-dimensional map of two-tone spectroscopy as a function of drive frequency ($f_d$) and parallel magnetic field $B$ for device 1. Four regimes are seen: (i) low fields ($0\text{–}40 \text{ mT}$), zeroth superconducting lobe, qubit frequency $f_Q$ decreases with increasing $B$; (ii) destructive regime, around half flux quantum $\Phi_0/2 \sim 50 \text{ mT}$, qubit coherence is lost; (iii) higher fields ($60\text{–}120 \text{ mT}$), first lobe, coherence is recovered with slightly reduced $f_Q$; and (iv) second destructive regime at $\sim 135 \text{ mT}$ where coherence is again lost. (b) Experiment (black points) and theory (orange curve) for qubit frequency, $f_Q$. Width of theory curve marks 3rd and 97th percentiles of the fit.

FIG. 3. (a) Rabi oscillations (black points) in the zeroth lobe ($B = 0$) in device 1 with best fit exponentially decaying sinusoidal oscillation, $A \exp(-\tau/T^R) \sin(\omega \tau + \phi) + C$ (orange) as a function of pulse duration $\tau$ (with $T_R$, $\alpha$, $\phi$, $C$, and $A$ as fit parameters) and yields a Rabi decay time of $T^R = 0.18 \mu$s. Qubit lifetime in the zeroth lobe was measured by exciting the qubit using the $\pi$ pulse, the length of which is found from Fig. 3(a), and measuring the qubit response after a time $\tau$, yielding $T_1 = 2.5 \mu$s. In the first lobe ($B = 100 \text{ mT}$), the Rabi decay time $T^R = 0.34 \mu$s was measured with relaxation time $T_1 = 0.5 \mu$s at $f_Q = 3.75 \text{ GHz}$, which is somewhat shorter than in the zeroth lobe, which could be attributed to dissipation from subgap states present in the first lobe [20] (see the Supplemental Material [39]). We believe that the modest increase in Rabi decay time in the first lobe is related to unintentional detuning of the drive frequency in the zeroth lobe data [Fig. 3(a)]. Transport measurements were performed by setting $V_{FETC}$ positive. Superconductor-insulator-superconductor spectroscopy in the first lobe showed no clear Majorana signatures, that is,

Details of the fitting procedure are given in an accompanying analysis notebook [38].

Time-domain measurements in the zeroth and first lobes are compared in Fig. 3. In the zeroth lobe ($B = 0$), Rabi oscillations with qubit drive frequency $f_d$ set to match $f_Q = 4.53 \text{ GHz}$ were measured [Fig. 3(a)]. Data (black points) are shown together with the best fit to an exponentially decaying sinusoidal oscillation, $A \exp(-\tau/T^R) \sin(\omega \tau + \phi) + C$ (orange) as a function of pulse duration $\tau$ (with $T_R$, $\alpha$, $\phi$, $C$, and $A$ as fit parameters) and yields a Rabi decay time of $T^R = 0.18 \mu$s. Qubit lifetime in the zeroth lobe was measured by exciting the qubit using the $\pi$ pulse, the length of which is found from Fig. 3(a), and measuring the qubit response after a time $\tau$, yielding $T_1 = 2.5 \mu$s. In the first lobe ($B = 100 \text{ mT}$), the Rabi decay time $T^R = 0.34 \mu$s was measured with relaxation time $T_1 = 0.5 \mu$s at $f_Q = 3.75 \text{ GHz}$, which is somewhat shorter than in the zeroth lobe, which could be attributed to dissipation from subgap states present in the first lobe [20] (see the Supplemental Material [39]).

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one cannot place an experimental bound on $E_M$ away from zero.

We next examine charge dispersion in the two lobes in device 2. The fine-scale dependence of the qubit transition frequency on gate voltage $V_C$, swept over a small range, is shown in Fig. 4(a). The interlaced sinusoidal qubit response as a function of $V_C$ (column average subtracted) represents the two parity branches, visible in the offset-charge-sensitive regime, as investigated previously in conventional [31] and semiconducting junctions [12,13]. The simultaneous visibility of both parity branches indicates parity switching (poisoning) that is faster than data acquisition time. (b) Coherent oscillations of both parity branches in the zeroth lobe ($B = 0$) are shown in Fig. 4(b) [qubit response $V_H(\tau = 0)$ subtracted from all columns for better visibility] and are measured at a more positive $V_C$, which increased the qubit frequency and slightly reduced dispersion. Rabi oscillations as a function of qubit drive time $\tau$ and drive frequency, $f_d$, are similar in the two parity branches. Comparable measurements in the first lobe ($B = 104$ mT), are shown in Figs. 4(c) and 4(d). We note that data in Figs. 4(b) and 4(d) were measured at $V_C$ values producing the largest frequency difference between the two parity branches at that particular qubit frequency. The slow drift that is visible in Fig. 4(c) is related to a small change in the junction conductance, which only changes considerably over a larger scale of $V_C$. Overall, no clear splitting at the parity crossing can be resolved here in Fig. 4(c) or in a broader range of gate voltages. We are able to place an upper bound, $E_M/h < 10$ MHz [38] based on the absence of a well-resolved splitting. We do not know if the absence of resolvable splitting of the parity branches reflects an absence of zero-energy states (due to the lack of tunability of material parameters), their negligible coupling across the junction (due to the sensitivity to electrostatic environment), or a short coherence due to rapid poisoning [6,7,32] from other low energy subgap states in the first lobe.

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